

TSM25N03

25V N-Channel MOSFET

TO-252



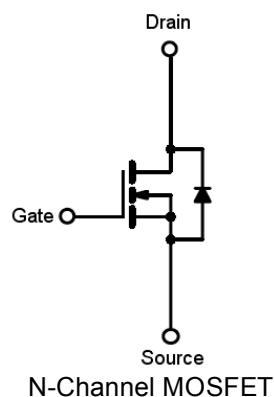
Pin Definition:

1. Gate
2. Drain
3. Source

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)
25	14 @ $V_{GS} = 10V$	25
	19 @ $V_{GS} = 4.5V$	25

Block Diagram



Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

Application

- Load Switch
- Dc-DC Converters and Motors Drivers

Ordering Information

Part No.	Package	Packing
TSM25N03CP RO	TO-252	2.5Kpcs / 13" Reel

Absolute Maximum Rating ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	25	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current, $V_{GS} @ 4.5V$.	I_D	25	A
Pulsed Drain Current, $V_{GS} @ 4.5V$	I_{DM}	100	A
Continuous Source Current (Diode Conduction) ^{a,b}	I_S	20	A
Single Pulse Drain to Source Avalanche Energy ($V_{DD} = 100V$, $V_{GS} = 10V$, $I_{AS} = 2A$, $L = 10mH$, $R_G = 25\Omega$)	EAS	45	mJ
Maximum Power Dissipation	P_D	60	W
		23	
Operating Junction Temperature	T_J	+150	$^\circ\text{C}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T_L	10	S
Junction to Case Thermal Resistance	$R_{\theta JC}$	1.8	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\theta JA}$	40	$^\circ\text{C/W}$

Notes:

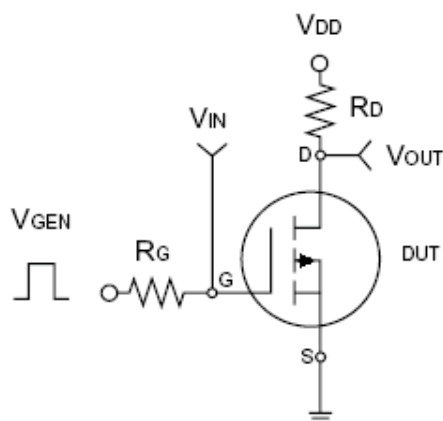
- a. Maximum DC current limited by the package
- b. Surface Mounted on 1" x 1" FR4 Board, $t \leq 10$ sec.

Electrical Specifications (Ta = 25°C unless otherwise noted)

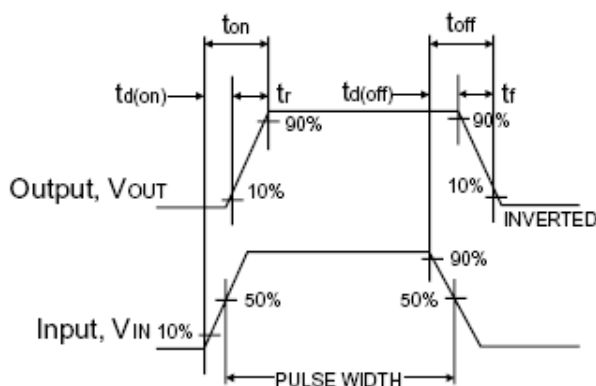
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	25	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	1.0	1.9	3.0	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	I_{DSS}	--	--	1.0	μA
On-State Drain Current	$V_{DS} \geq 5V, V_{GS} = 10V$	$I_{D(ON)}$	25	--	--	A
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 25A$	$R_{DS(ON)}$	--	14.5	19	m Ω
	$V_{GS} = 10V, I_D = 25A$		--	9.5	14	
Forward Transconductance	$V_{DS} = 15V, I_D = 15A$	g_{fs}	--	12	--	S
Diode Forward Voltage	$I_S = 20A, V_{GS} = 0V$	V_{SD}	--	0.87	1.5	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 15V, I_D = 25A, V_{GS} = 10V$	Q_g	--	14.7	26	nC
Gate-Source Charge		Q_{gs}	--	2.5	--	
Gate-Drain Charge		Q_{gd}	--	3	--	
Input Capacitance	$V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$	C_{iss}	--	921	--	pF
Output Capacitance		C_{oss}	--	208.7	--	
Reverse Transfer Capacitance		C_{rss}	--	108.2	--	
Switching ^c						
Turn-On Delay Time	$V_{DD} = 15V, R_L = 15\Omega, I_D = 1A, V_{GEN} = 10V, R_G = 16\Omega$	$t_{d(on)}$	--	20.2	--	nS
Turn-On Rise Time		t_r	--	5.9	--	
Turn-Off Delay Time		$t_{d(off)}$	--	49.5	--	
Turn-Off Fall Time		t_f	--	16.7	--	

Notes:

- pulse test: $PW \leq 300\mu S$, duty cycle $\leq 2\%$
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.



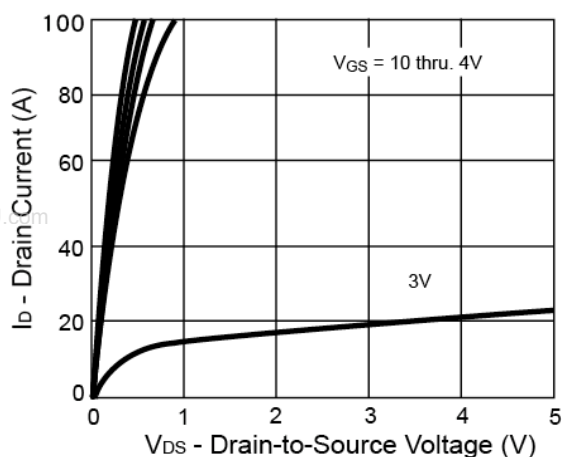
Switching Test Circuit



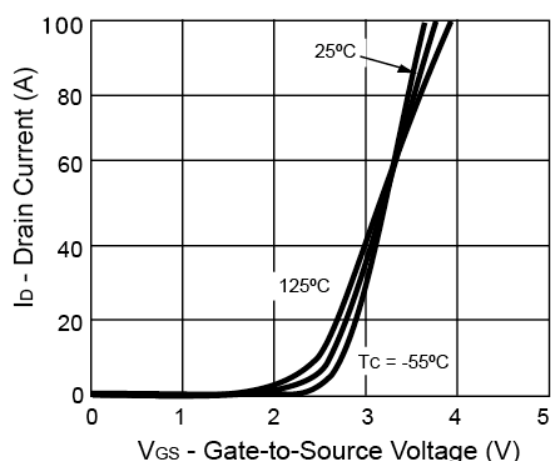
Switchin Waveforms

Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

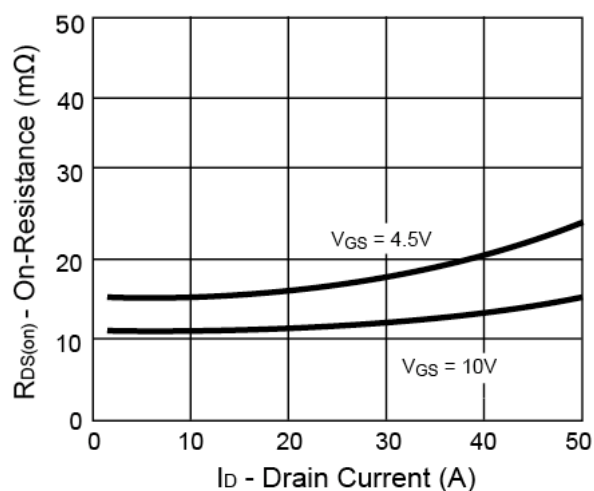
Output Characteristics



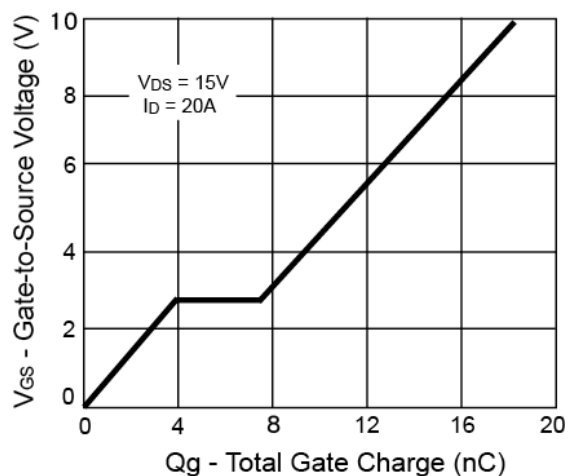
Transfer Characteristics



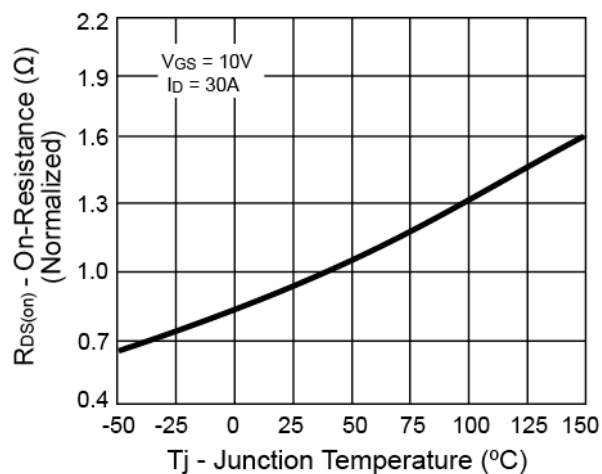
On-Resistance vs. Drain Current



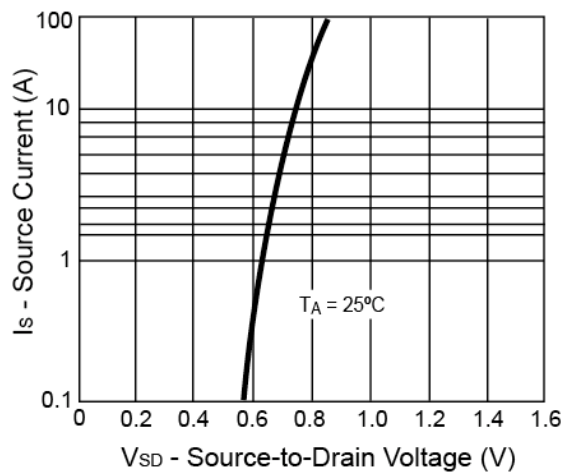
Gate Charge



On-Resistance vs. Junction Temperature

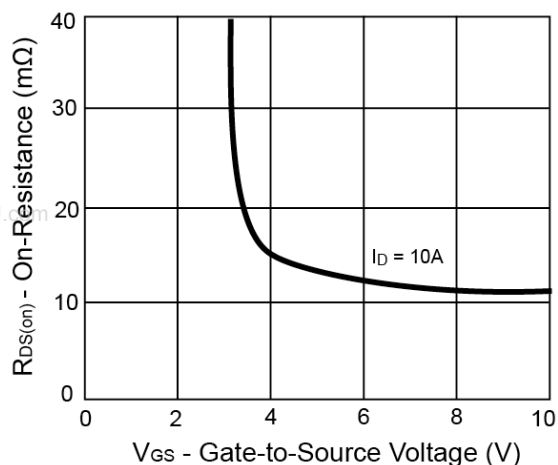


Source-Drain Diode Forward Voltage

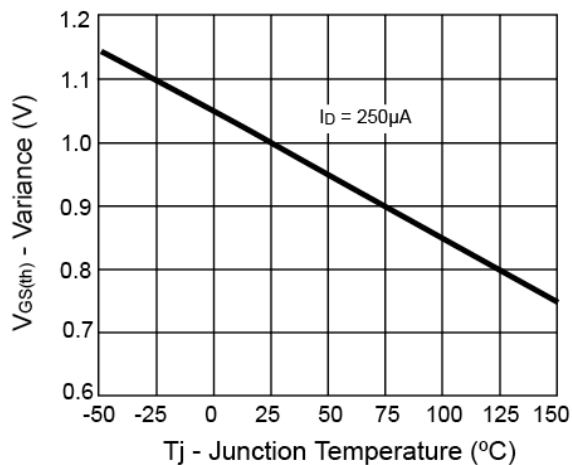


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

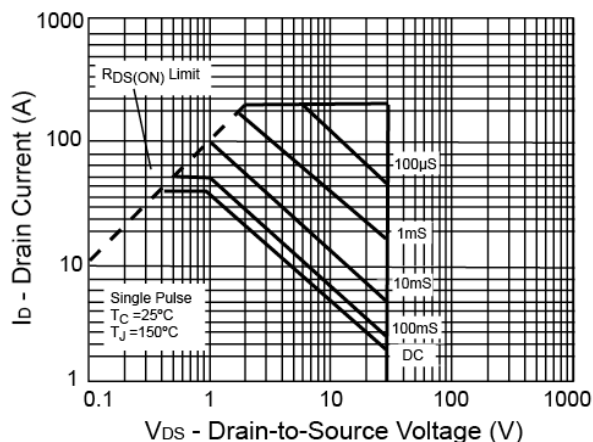
On-Resistance vs. Gate-Source Voltage



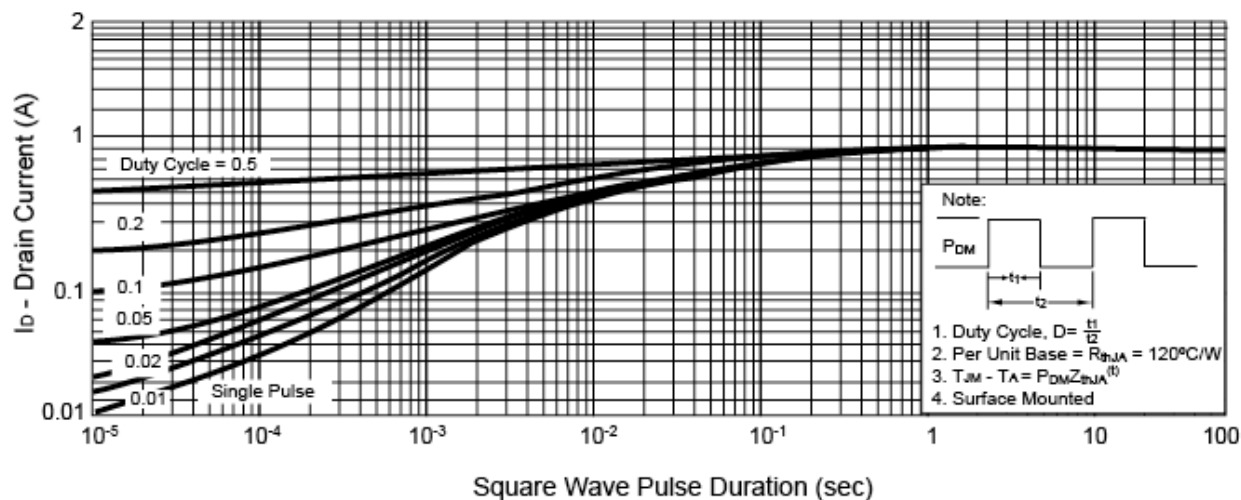
Threshold Voltage



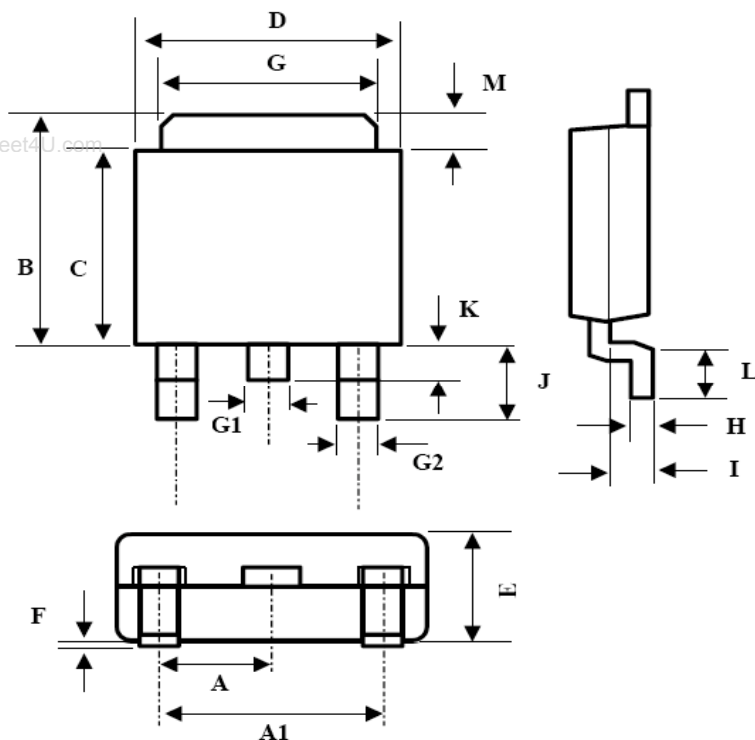
Maximum Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

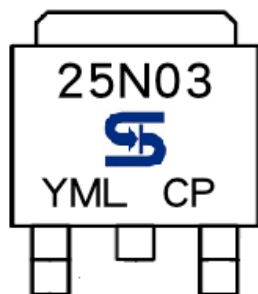


SOT-252 Mechanical Drawing



DIM	TO-252 DIMENSION			
	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.3BSC		0.09BSC	
A1	4.6BSC		0.18BSC	
B	6.80	7.20	0.268	0.283
C	5.40	5.60	0.213	0.220
D	6.40	6.65	0.252	0.262
E	2.20	2.40	0.087	0.094
F	0.00	0.20	0.000	0.008
G	5.20	5.40	0.205	0.213
G1	0.75	0.85	0.030	0.033
G2	0.55	0.65	0.022	0.026
H	0.35	0.65	0.014	0.026
I	0.90	1.50	0.035	0.059
J	2.20	2.80	0.087	0.110
K	0.50	1.10	0.020	0.043
L	0.90	1.50	0.035	0.059
M	1.30	1.70	0.051	0.67

Marking Diagram



- Y** = Year Code
M = Month Code
 (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
L = Lot Code

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